

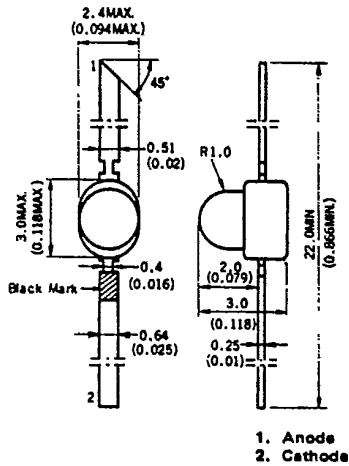
LIGHT EMITTING DIODE SE302A

GaAs INFRARED EMITTER INDUSTRIAL USE

DESCRIPTION

The SE302A is a GaAs (Gallium Arsenide) Infrared Light Emitting Diode which is mounted on the lead frame and molded in clear plastic lens. On forward bias, it emits a spectrally narrow band of radiation peaking at 940nm. The close wavelength match of this device to silicon sensors makes it ideally suited for all source-sense applications. Its low cost and volume producibility open new areas of use anywhere an infrared source is desirable.

PACKAGE DIMENSIONS in millimeters (inches)



* Soldering conditions are at 260°C or less within 5sec. at 3 mm or farther from the case.

FEATURES

- Low cost.
- High Output Power
- Fast Switching Time.
- Long Life-Solid State Reliability.
- Compact, Rugged, Lightweight.
- Spectrally Matched to Silicon Sensors. (Good Compatibility with darlington Photo transistor (PH101).)
- Easily assembled in linear arrays.
- Compatible with integrated circuits.

APPLICATIONS

- Electro optical switches.
- Card and tape reader sources.
- Optical Encoders.
- Photochoppers, Isolator.
- High Speed Optoelectronic Data Links.
- Photo coupler.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation (Ta = 25°C)	P	75	mW
Maximum Forward Current (Ta = 25°C)	IF	50	mA
Maximum Reverse Voltage (Ta = 25°C)	VR	3.0	V
Maximum Temperatures			
Junction Temperature	Tj	80	°C
Storage Temperature	Tstg	-30 to +80	°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Forward Voltage	VF		1.2	1.4	V	IF = 30 mA
Reverse Current	IR			50	µA	VR = 3.0V
Capacitance	C		100		pF	V = 0, f = 1.0 MHz
Peak Emission Wavelength	λpeak		940		nm	IF = 30 mA
Spectral Line Half Width	Δλ		60		nm	IF = 30 mA
Output Power	PO	1.0	1.5		mW	IF = 30 mA
Light Turn-On and Turn-Off	ton, toff		1.0		µs	IF = 30 mA

* f = 1.0 kHz, duty cycle 1%

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

